N-Channel Silicon MOSFET



#### Features

- · Low ON resistance.
- · Ultrahigh-speed switching.
- · High-speed diode (trr=100ns).

### Package Dimensions



# **Specifications**

### Absolute Maximum Ratings at $Ta = 25^{\circ}C$

Parameter	Symbol	Conditirins	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		600	V
Gate-to-Source Voltage	VGSS		±30	V
Drain Current (DC)	10		2	Α
Drain Current (pulse)	I <sub>DP</sub>		8	Α
Allowable Power Dissipation	PD		1.75	W
	י D ידc=בס-ט		50	W
Channel Temperature	Tch		150	°C
Storage Temperature	rstg	//	-55 to +150	°C

## Electrical Characteristics at Ta = `5°C

Parameter		Conditions		Ratings		
		Conditions	min	typ	max	Unit
Drain-to-Source Breakdowr Vr Itage	V(BR)DSS	=10mA, V <sub>GS</sub> =0	600			V
Zero-Gate Votlage Drain Cyrrent	I <sub>DSS</sub> V <sub>E</sub>	DS=480V, VGS=0			1.0	mA
Gate-to-Source Leakage Current	IGSS VC	GS=±30V, V <sub>DS</sub> =0			±100	nA
Cutoff Voltage	VrJS(off) VE	DS=10V, ID=1mA	2.0		3.0	V
Forward Transfer Ar mittance	yfs   V <sub>E</sub>	<sub>DS</sub> =10V, I <sub>D</sub> =1A	0.8	1.5		S
Static Drain-to-Source On tate Phoistance	KDS(on)	=1A, V <sub>GS</sub> =10V		3.2	4.3	Ω
(Note) Be car eff $d$ in hand $d$ = 28 19221	pe ause it has no prot	tection diode between gate and source		Contin	ued on n	ext nage

(Note) Be callef if in handling the 2S 1922 because it has no protection diode between gate and source

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Parameter	Symbol	Conditions	Ratings		Unit
Input Capacitance	Ciss	V <sub>DS</sub> =20V, f=1MHz	400		pF
Output Capacitance	Coss	V <sub>DS</sub> =20V, f=1MHz	55		pF
Reverse Transfer Capacitance	Crss	V <sub>DS</sub> =20V, f=1MHz	15		pF
Turn-ON Delay Time	<sup>t</sup> d(on)	See specified Test Circuit.	10		ns
Rise Time	tr	See specified Test Circuit.	12		ns
Turn-OFF Delay Time	td(off)	See specified Test Circuit.	65		ns
Fall Time	tf	See specified Test Circuit.	40	$\sim$	ns
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =2A, V <sub>GS</sub> =0		15	V
Diode Reverse Recovery Time	trr	I <sub>S</sub> =2A, di/dt=100A/µs	100	7	ns

#### **Switching Time Test Circuit**





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